[Image of handwritten notes and diagrams]
Very simple CMOS - 5 masks

Very similar structure

\[ I_0 \approx \frac{V_{DD} - V_T}{R} \] for some tech.

\[ V_{GS} \text{ (in n-type)} \]

Channel forms a nonliner

above a threshold

very well.

- \( R \) for \( \text{flux gates} \)
- \( \text{high junction \#1} \)
- \( \text{low junction \#2} \)
- \( \text{drain} \)
- \( \text{source} \)

\( \text{N-channel} \)

\( \text{P-channel} \)

\( \text{N WELL} \)

\( \text{P WELL} \)

\( \text{P} \)

\( \text{N} \)

\( \text{MOSFET - N-channel, oxide, source/drain} \)

\( \text{P-type substrate} \)

\( \text{N+} \)

\( \text{P+} \)

\( \text{N-} \)

\( \text{P-} \)

\( \text{VDD} \)

\( \text{GND} \)